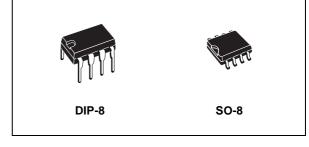


ADJUSTABLE INVERTING NEGATIVE OUTPUT CURRENT MODE PWM REGULATORS

- 2.7V TO 11V INPUT TO ADJUSTABLE NEGATIVE OUTPUT CONVERSION
- 1W GUARANTEED OUTPUT POWER (V_I > 4.5V, T ≤ 70°C)
- 68% TYP. EFFICENCY AT 6V
- VERY LOW QUIESCENT CURRENT: 1.2mA IN ON MODE, 10µA IN SHUT DOWN MODE
- SOFT START
- VERY LOW NOISE OUTPUT
- 160KHz FIXED FREQUENCY OSCILLATOR
- MIXED BIPOLAR-CMOS TECHNOLOGY



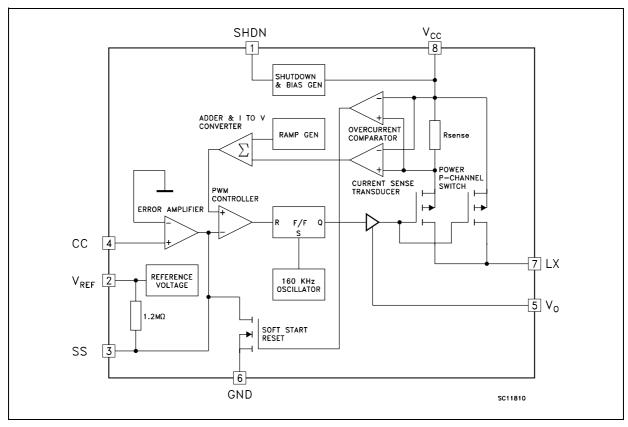
 $T_A = 0$ °C to 70°C) and 275mA (typical value at $T_A = 25$ °C, $V_O = -5$ V).

A logic controlled shut down pin that interfaces directly with microprocessor reduces supply current to only 10mA. Input to Output differential voltage is limited to $V_I + |V_O| < 12.7V$. No load supply current is 1.2mA.

DESCRIPTION

The ST755 is an adjustable inverting switch-mode DC-DC regulator with internal Power MOSFET that generators an adjustable negative output from a voltage input of 2.7V to 11V, output current guaranteed at 200mA (for $V_I > 4.5V$, $V_O = -5V$ and

SCHEMATIC DIAGRAM



June 2003 1/10

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter ²	Value	Unit
V _{CC}	DC Input Voltage to GND (Note1)	-0.3 to 12	V
V _{SHDN}	Shutdown Voltage, SS Voltage, CC Voltage	-0.3 to (V _{CC} + 0.3)	V
V_{LX}	Switch Voltage (LX to V _{CC})	-12.5 to + 0.3	V
V_{FB}	Feedback Voltage (V _O to GND)	-11 to + 0.9	V
I _{LX}	Peak Switch Current	2	Α
P _{TOT}	Continuous Power Dissipation at T _A = 70°C (DIP-8) (SO-8)	725 470	mW
T _{op}	Operating Junction Temperature Range (C series)	-40 to 185	°C
T _{stg}	Storage Temperature Range	-55 to +150	°C

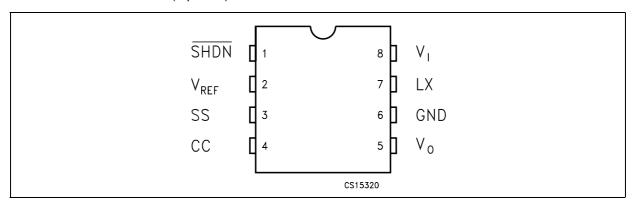
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. Note 1: The input to output differential voltage is limited to V_{CC} + $|V_O|$ <12.7V

THERMAL DATA

Symbol	Parameter	SO-8	DIP-8	Unit
R _{thj-amb}	Thermal Resistance Junction-ambient (*)	160	100	°C/W

^(*) This value depends from thermal design of PCB on which the device is mounted.

CONNECTION DIAGRAM (top view)



PIN DESCRIPTION

Pin N°	Symbol	Name and Function
1	SHDN	SHUT-DOWN control (V _{CC} = ON, GND = Shutdown)
2	V _{REF}	Reference Output Voltage: (1.25V)
3	SS	Soft Start
4	CC	Compensation Input
5	Vo	Negative Output Voltage
6	GND	Ground
7	LX	Switch Output
8	V _{CC}	Supply Voltage Input.

ORDERING CODES

TYPE	DIP8	SO-8	SO-8 (T&R)
ST755	ST755CN	ST755CD	ST755CD-TR

ELECTRICAL CHARACTERISTICS (Refer to the test circuits, $V_{CC} = 5V$, $V_O = -5.25$ to -4.75V, $I_{LOAD} = 0$ mA, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise specified. Typical value are referred at $T_A = 25$ °C)

Symbol	Parameter	Test (Conditions	Min.	Тур.	Max.	Unit
VI	Input Voltage			4		11	V
Vo	Output Voltage	$V_{CC} = 4.5 \text{ to } 6.2 \text{V}$	I _O =0 to 200mA	4.75	5	5.25	V
Io	Output Current	$V_{CC} = 4.5 \text{ to } 6.2 \text{V}$	T _A = 0 to 70°C	200	275		mA
		$V_{CC} = 4.5 \text{ to } 6.2 \text{V}$	$T_A = -40 \text{ to } 85^{\circ}\text{C}$	175			
		V _{CC} = 4V	V _O = -5V		175		
		V _{CC} = 2.7V	V _O = -5V		125		
I _{SUPPLY}	Supply Current (Including Switching Current)	No Load	$V_{SHDN} = V_{CC}$		1.2	3.5	mA
I _{OFF}	Standby Current)	No Load	V _{SHDN} = 0V		10	100	μΑ
I _{SC}	Short Circuit Current)				1.2		Α
ΔV_{O}	Line Regulation	$V_{CC} = 4 \text{ to } 6.2V$			0.1		%/V
ΔV_{O}	Load Regulation	I _O = 0 to 200mA			0.003		%/mA
V_{REF}	Reference Voltage	T _A = 25°C		1.18	1.25	1.32	V
ΔV_{REF}	Reference Drift	$T_A = T_{MIN}$ to T_{MAX}			50		ppm/°C
R _{DSON}	LX On Resistance				0.7		Ω
I _{LEAK}	LX Leakage Current)	V _{DS} = 10V			1		μA
I _{SH}	Shutdown Pin Current)					1	μA
V_{IH}	SHDN Input High Threshold			2			V
V_{IL}	SHDN Input Low Threshold					0.25	V
fosc	Oscillator Frequency				160		KHz
η	Power Efficiency	I _O =100mA			68		%
CC	Compensation Pin Impedance				7.5		ΚΩ

Do not overload or short the Output to Ground. If the above conditions are observed, the device may be damaged.

APPLICATION INFORMATION

The ST755 is an IC developed for voltage conversion from an input voltage ranging from ± 2.4 V to 11V to a regulated adjustable negative output limited by $|V_O| \le 12.7$ V- $|V_O|$. The circuit adopts a current-mode PWM control scheme to achieve good efficiency, high stability and low noise performance. The figure in the first page shown the detailed block diagram of the device.

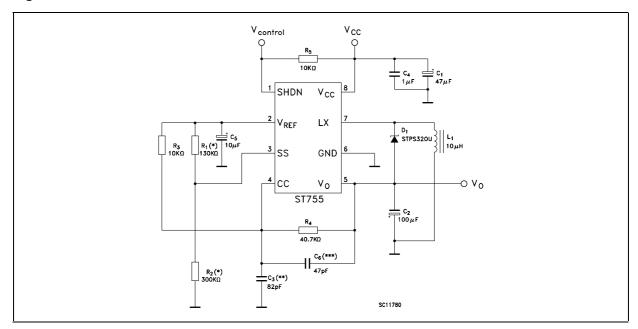
ST755 is realized in a BCD technology in order to achieve high temperature stability, the best REFERENCE precision, a very low quiescent current and jitter free operations. The final stage is built around a 0.7Ω - 2A P-Channel Power MOS. A fraction of the output current is splitted out for current detection.Internal clock frequency is fixed to 160KHz. Error amplifier drives the PWM comparator in order to keep 0V on the CC input. So R_3 and R_4 resistors are calculated by the following formulae R_4 = ($|V_O|/V_{REF}|^*R_3$ (see fig 1). For R_3 can be choose any value between 2K Ω and 20K Ω . Soft-Start (SS) input is a voltage dependent-output current limit (see figure 9, Switch Current Limit vs. SS Input Voltage). SS pin is internally pulled to V_{REF} through a 1.2 M Ω resistor. Applying an appropriate capacitor at SS input is possible to obtain a soft-start current imitation during power up. Forcing Soft-Start (SS) input to a lower voltage through a resistive voltage driver (R_1 and R_2), the maximum LX current limit can be lowered according the diagram showed in figure 9. When SHDN input is low, the total current consumption is reduced to $10\mu A$.

APPLICATION CIRCUIT

To achieve the best performances from switching power supply topology, particular care to layout drawing is needed, in order to minimize EMI and obtain low noise, jitter free operation moreover, it ensures the full device functionality. Layout design proposed on demoboard (see picture 2) helps to lower the developing

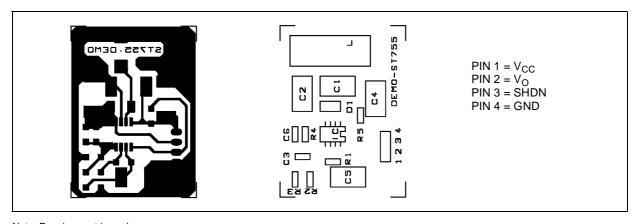
time. Wire lengths must be minimized, filter and by-pass capacitors C_1 , C_2 and C_3 must be low ESR type, placed as close possible to the integrated circuit. The $10\mu H$ inductor must be chosen built on a core, taking care that saturation current should be higher than the peak LX switch current. See the PEAK INDUCTOR CURRENT vs. LOAD CURRENT graph (figure 6).

Figure 1: TYPICAL APPLICATION CIRCUIT



- (*) R1 and R2 can be omitted for lout<200mA.
 (**) C6: Very low noise but poor transient and load response speed.
 (***) C3 (alternative to C6): faster transient and load response.

Figure 2: PRINTED DEMOBOARD



Note: Drawings not in scale Component Values

Capacitor	Value	Unit	Resistor	Value	Unit
C1	47	μF	R1	130	ΚΩ
C2	100	μF	R2	300	ΚΩ
C3	82	pF	R3	10	ΚΩ
C4	1	μF	R4	40.7	ΚΩ
C5	10	μF	R5	10	ΚΩ
C6	47	pF			

TYPICAL PERFORMANCE CHARACTERISTICS (unless otherwise specified T_i = 25°C

Figure 3: Load Current vs Supply Voltage

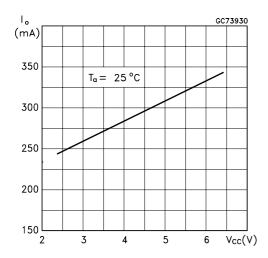


Figure 4: Load Current vs Supply Voltage

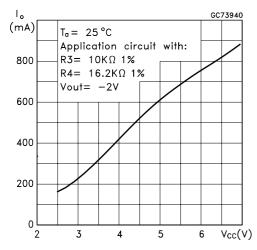


Figure 5: Efficiency vs Load Current

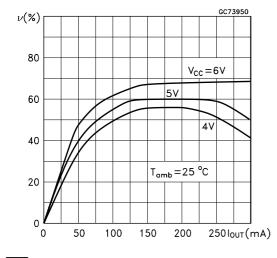


Figure 6: Peak Inductor Current vs Load Current

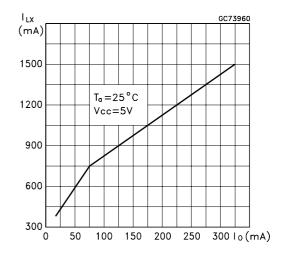


Figure 7 : Switch ON Resistance vs Supply Voltage

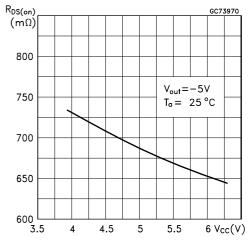
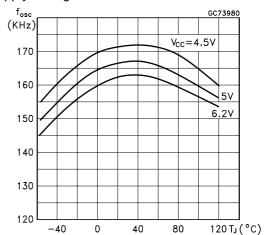


Figure 8 : Oscillator Frequency vs Temperature & Supply Voltage



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Figure 9 : Switch Current Limit vs Soft Start Voltage

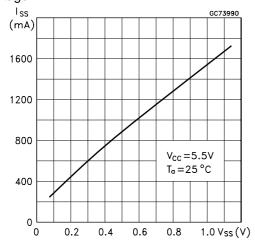


Figure 10 : Reference Voltage Vs Temperature

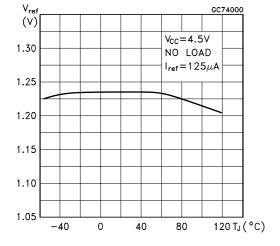
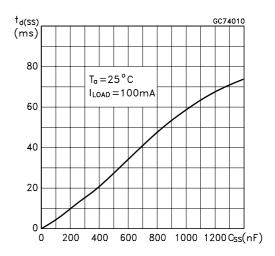
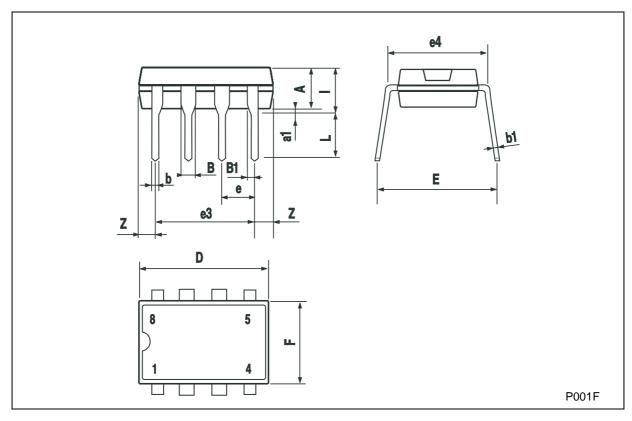


Figure 11 : Soft Start Delay Time



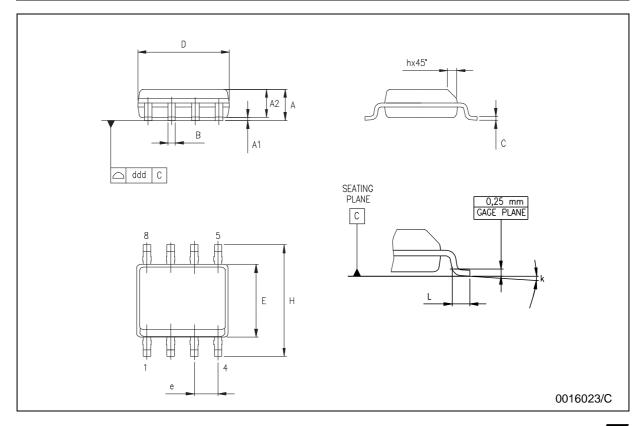
Plastic DIP-8 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А		3.3			0.130	
a1	0.7			0.028		
В	1.39		1.65	0.055		0.065
B1	0.91		1.04	0.036		0.041
b		0.5			0.020	
b1	0.38		0.5	0.015		0.020
D			9.8			0.386
E		8.8			0.346	
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			7.1			0.280
I			4.8			0.189
L		3.3			0.130	
Z	0.44		1.6	0.017		0.063



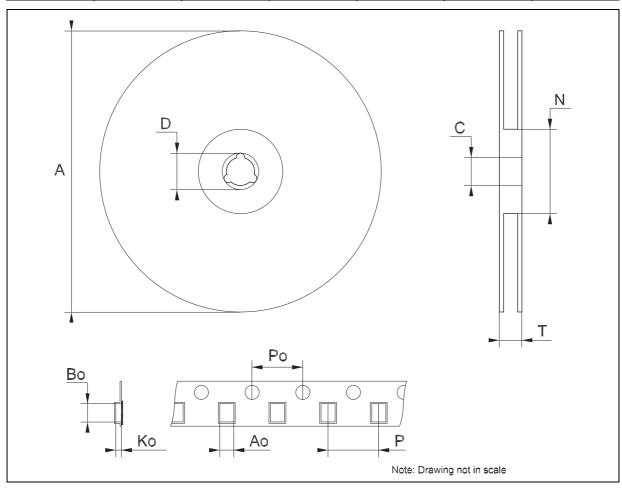
SO-8 MECHANICAL DATA

DIM.		mm.			inch	•	
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	1.35		1.75	0.053		0.069	
A1	0.10		0.25	0.04		0.010	
A2	1.10		1.65	0.043		0.065	
В	0.33		0.51	0.013		0.020	
С	0.19		0.25	0.007		0.010	
D	4.80		5.00	0.189		0.197	
E	3.80		4.00	0.150		0.157	
е		1.27			0.050		
Н	5.80		6.20	0.228		0.244	
h	0.25		0.50	0.010		0.020	
L	0.40		1.27	0.016		0.050	
k	8° (max.)						
ddd			0.1			0.04	



Tape & Reel SO-8 MECHANICAL DATA

D.114		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			22.4			0.882
Ao	8.1		8.5	0.319		0.335
Во	5.5		5.9	0.216		0.232
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319



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